

AMENDMENTS TO THE CLAIMS

Claim 1 (currently amended): An integrated circuit including

- a patterned copper layer,
- a patterned aluminum layer,
- a stud connection in an opening in a layer of material between a location on said patterned copper layer and a location on said patterned aluminum layer, said stud connection being formed of tungsten, and

- a liner in said opening and extending between said stud connection and said location on said patterned copper layer.

Claim 2 (original): An integrated circuit as recited in claim 1 wherein said liner comprises

- a layer of tantalum nitride, and
- a layer of PVD tungsten.

Claim 3 (original): An integrated circuit as recited in claim 1 wherein said liner comprises

- a layer of titanium, and
- a layer of titanium nitride or PVD tungsten.

Claim 4 (cancelled)

Claim 5 (original): An integrated circuit as recited in claim 1 wherein said patterned aluminum layer includes a layer of at least one of titanium and titanium nitride.

Claim 6 (original): An integrated circuit as recited in claim 2 wherein said patterned aluminum layer includes a layer of at least one of titanium and titanium nitride.

Claim 7 (original): An integrated circuit as recited in claim 3 wherein said patterned aluminum layer includes a layer of at least one of titanium and titanium nitride.

Claim 8 (cancelled)

Claim 9 (original): An integrated circuit as recited in claim 1, further including a covering layer.

Claim 10 (original): An integrated circuit as recited in claim 9 wherein said covering layer includes a layer of silane-based high density plasma oxide.

Claims 11-16 (withdrawn)